



SILICON N-CHANNEL RF POWER MOSFET

DESCRIPTION:

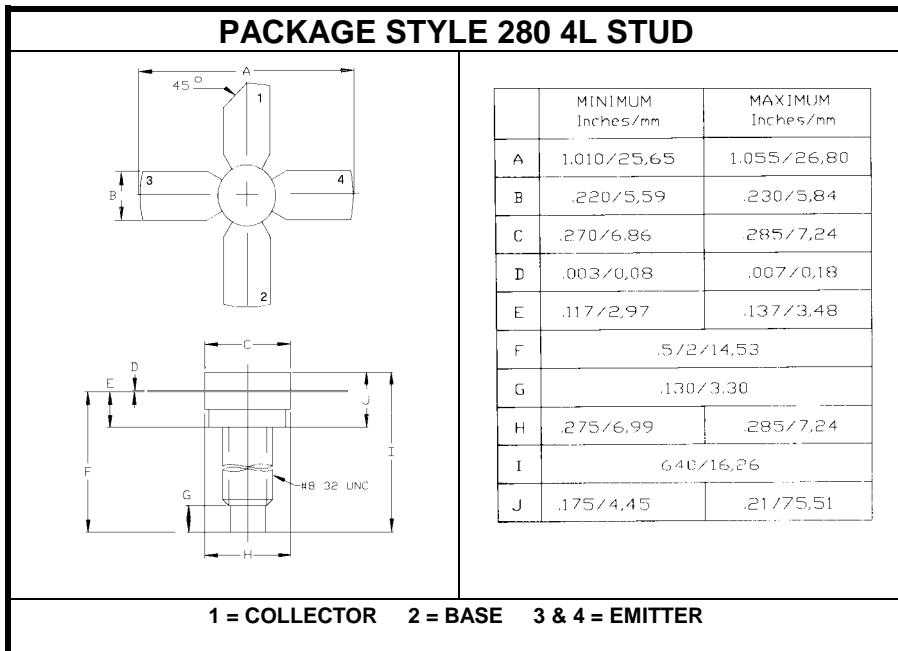
The **TPV596** is Designed for Common Source Push Pull RF Power Applications up to 400 MHz.

FEATURES:

- $P_G = 12$ dB min. at 0.5 W/ 860 MHz
- Common Emitter
- **Omnigold™** Metallization System

MAXIMUM RATINGS

I_C	0.7 A
V_{CE}	24 V
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
P_{DISS}	8.75 W @ $T_C = 25$ °C



CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 20$ mA	24			V
BV_{CBO}	$I_C = 1.0$ mA	45			V
BV_{CER}	$I_C = 20$ mA $R_{BE} = 10$ Ω	50			V
BV_{EBO}	$I_E = 0.25$ mA	3.5			V
I_{CBO}	$V_{CB} = 28$ V			0.45	mA
h_{FE}	$I_C = 100$ mA $V_{CE} = 5.0$ V	15		120	---
C_{OB}	$V_{CB} = 28$ V $f = 1.0$ MHz			5.0	pF
P_G	$V_{CE} = 20$ V $I_E = 0.22$ A $f = 860$ MHz	11.5	12		dB